
HL6325/26G

Low Operating Current Visible Laser Diode

HITACHI

ADE-208-781A (Z)
2nd Edition
Jul. 1999

Description

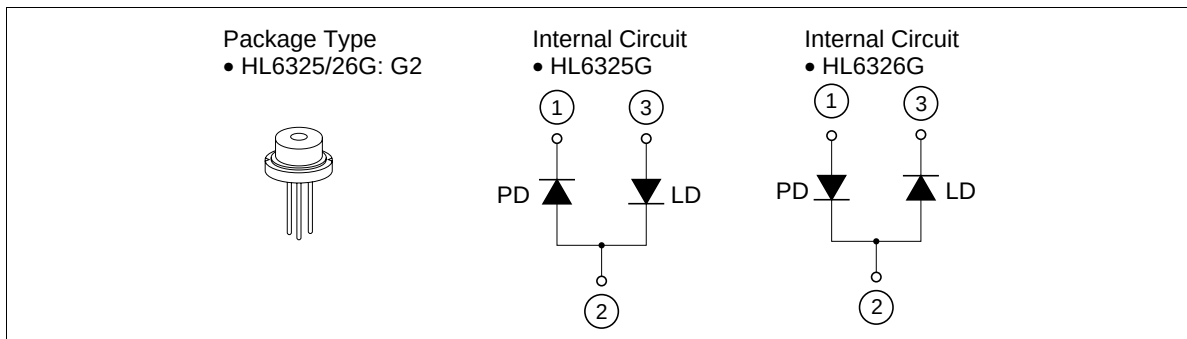
The HL6325/26G are 0.63 μm band AlGaInP laser diodes with a multi-quantum well (MQW) structure. They are suitable as light sources for laser levelers, laser scanners and optical equipment for measurement.

Application

- Laser leveler
- Laser scanner
- Measurement

Features

- Visible light output : 635 nm Typ (nearly equal to He-Ne gas laser)
- Optical output power : 5 mW CW
- Low operating current : 40 mA Typ
- Low operating voltage : 2.4 V Max
- Operating temperature : +60°C
- TM mode oscillation



HL6325/26G

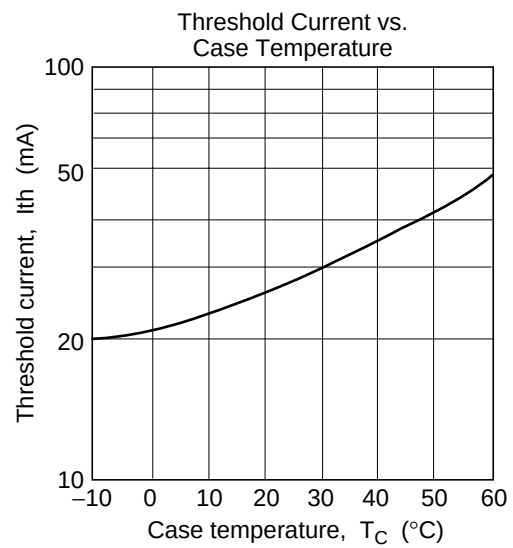
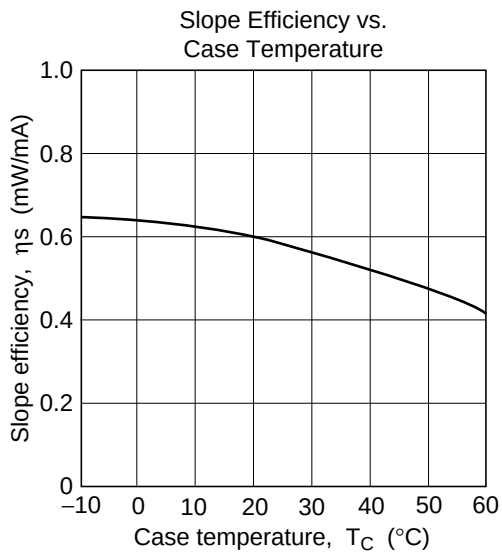
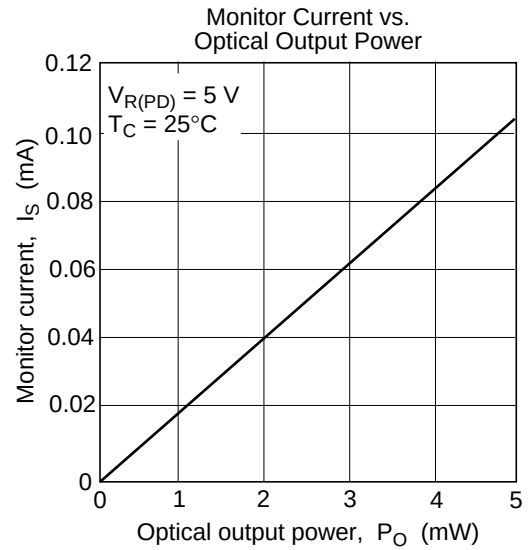
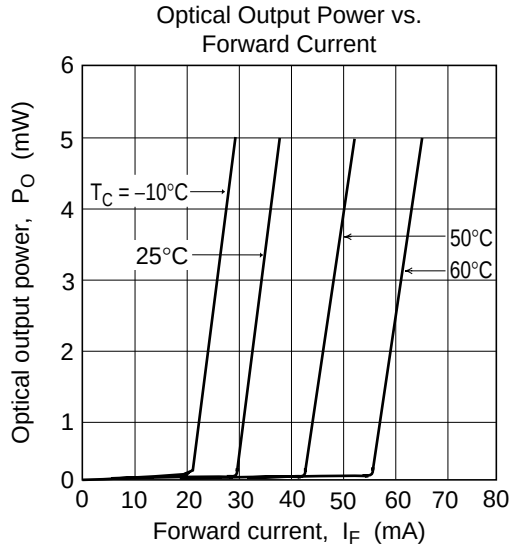
Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

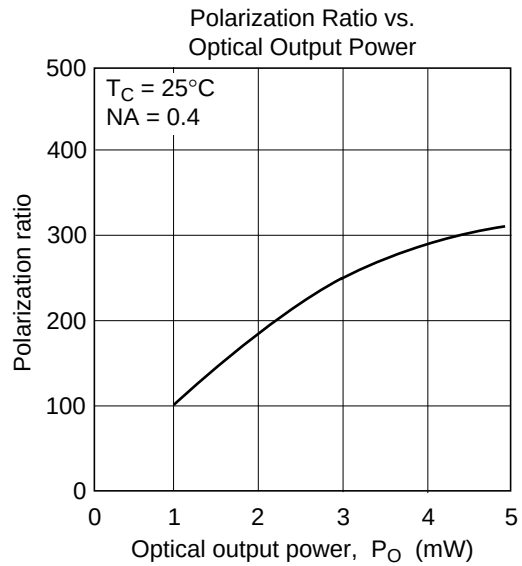
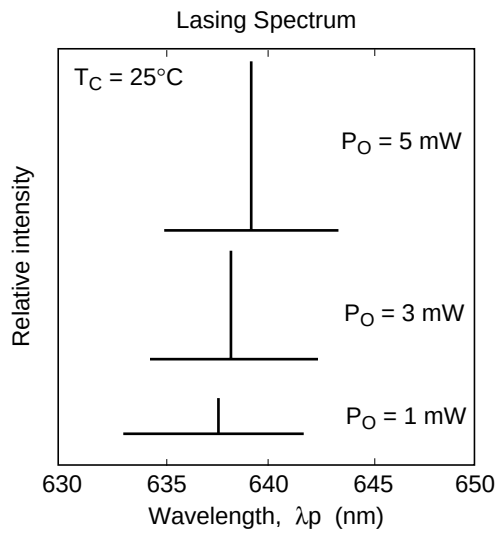
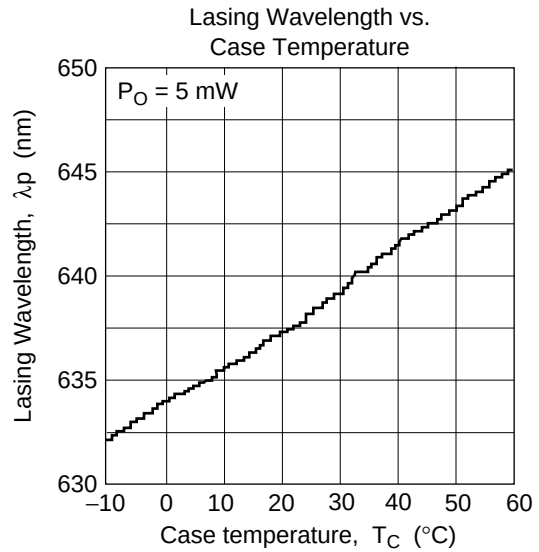
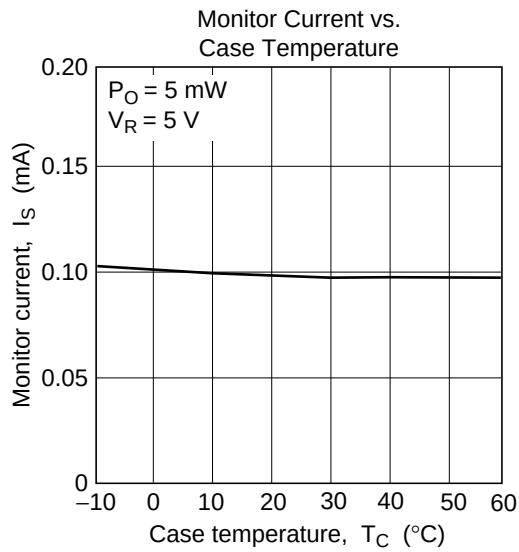
Item	Symbol	Value	Unit
Optical output power	P_O	5	mW
LD reverse voltage	$V_{R(LD)}$	2	V
PD reverse voltage	$V_{R(PD)}$	30	V
Operating temperature	T_{opr}	-10 to +60	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

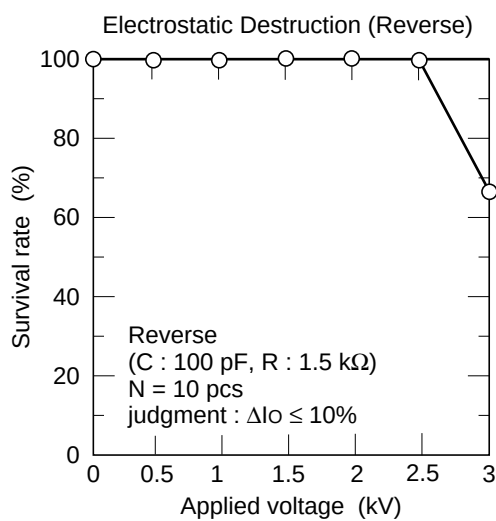
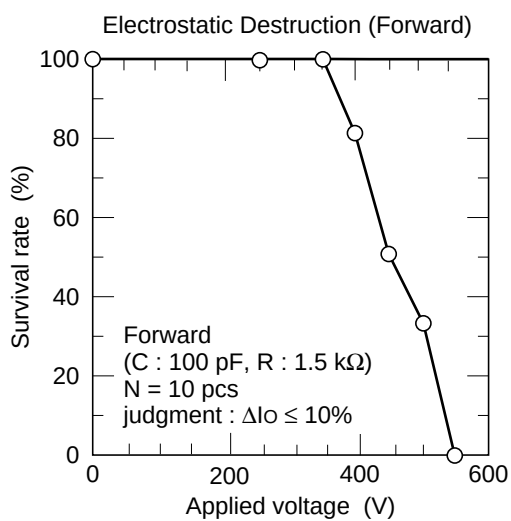
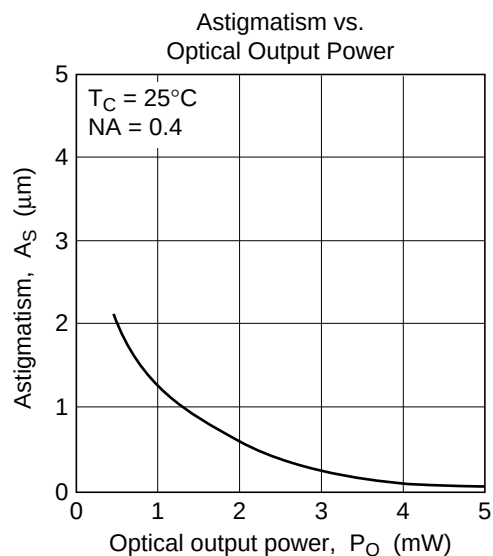
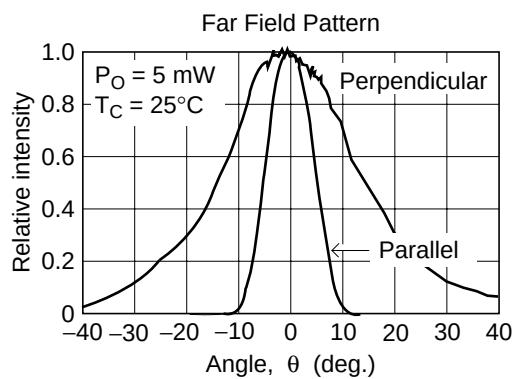
Optical and Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Optical output power	P_O	5	—	—	mW	Kink free
Threshold current	I_{th}	—	30	50	mA	
Operating current	I_{op}	—	40	60	mA	$P_O = 5 \text{ mW}$
Operating voltage	V_{OP}	—	2.2	2.4	V	$P_O = 5 \text{ mW}$
Slope efficiency	η_s	0.3	0.5	0.8	mW/mA	$3(\text{mW}) / (I_{(4\text{mW})} - I_{(1\text{mW})})$
Lasing wavelength	λ_p	630	635	640	nm	$P_O = 5 \text{ mW}$
Beam divergence parallel to the junction	$\theta_{//}$	6	8	11	deg.	$P_O = 5 \text{ mW}$
Beam divergence perpendicular to the junction	$\theta_{\perp}$	25	31	37	deg.	$P_O = 5 \text{ mW}$
Monitor current	I_s	0.05	0.1	0.25	mA	$P_O = 5 \text{ mW}, V_{R(PD)} = 5\text{V}$

Typical Characteristic Curves



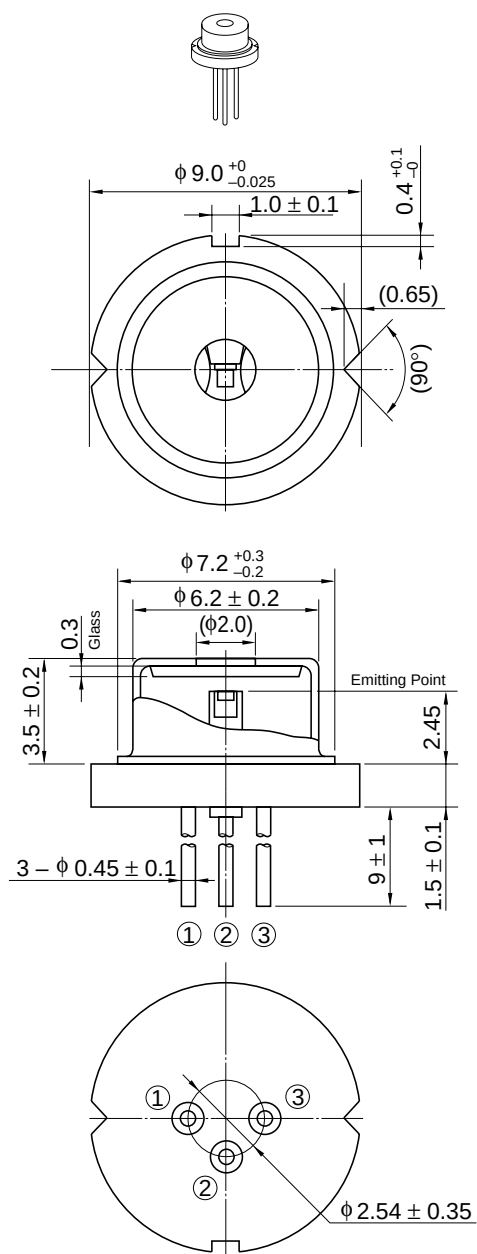




HL6325/26G

Package Dimensions

Unit: mm



Hitachi Code	LD/G2
JEDEC	—
EIAJ	—
Weight (reference value)	1.1 g

Cautions

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1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.

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